

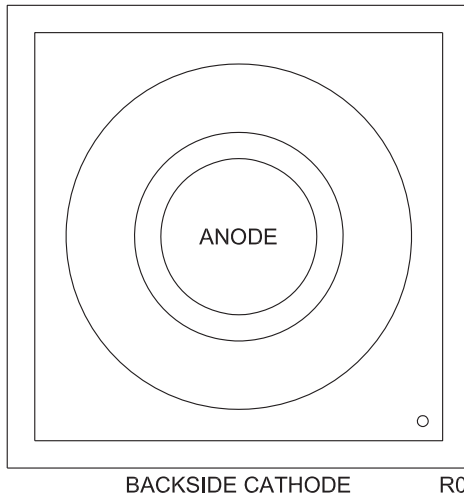
PROCESS CPD66X
Low Leakage Diode
Low Leakage Diode Chip



PROCESS DETAILS

| | |
|------------------------|-------------------|
| Die Size | 17.5 x 17.5 MILS |
| Die Thickness | 5.9 MILS |
| Anode Bonding Pad Area | 7.9 MILS DIAMETER |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au-As - 13,000Å |

GEOMETRY



GROSS DIE PER 5 INCH WAFER

54,848

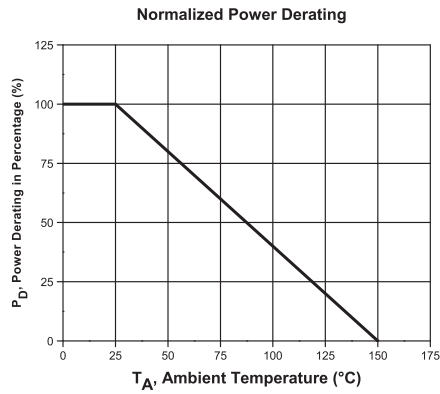
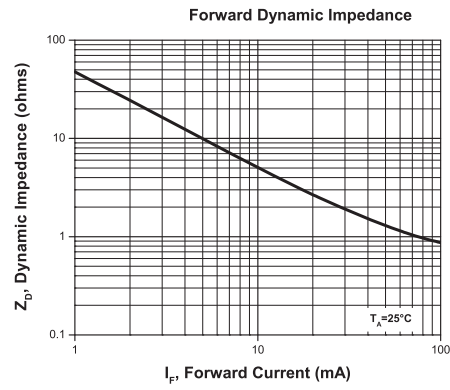
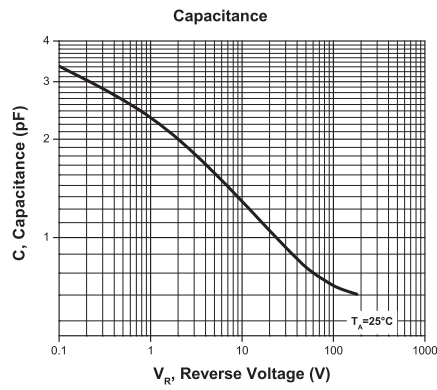
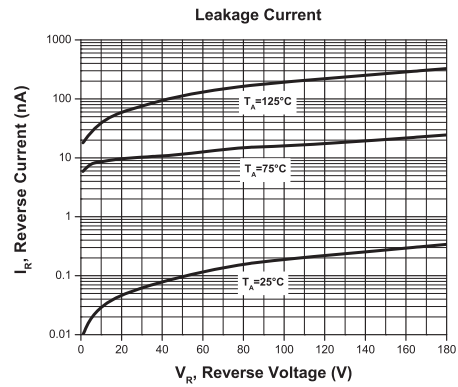
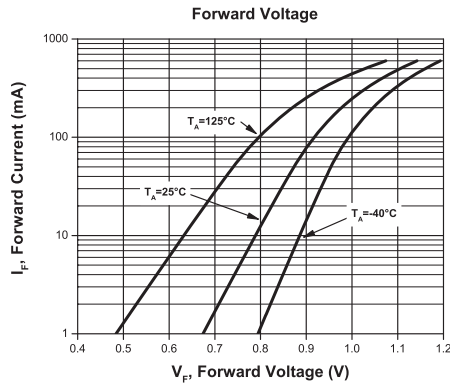
PRINCIPAL DEVICE TYPES

CMOD3003
CMLD3003DOG
CMPD3003A
CMPD3003C
CMPD3003S

R1 (19-July 2010)

PROCESS CPD66X

Typical Electrical Characteristics



R1 (19-July 2010)